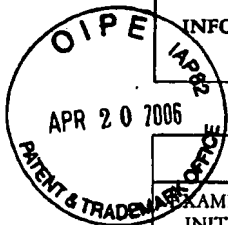


Form 1449*	Docket Number: G&C 30794.94-US-WO	Application Number: 10/537,385
INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION		
Applicant: Benjamin A. Haskell et al.		
Filing Date: June 3, 2005	Group Art Unit: <del>2841</del> 2824	



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	Applicant: Benjamin A. Haskell et al.	
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<b>Form 1449*</b> <b>INFORMATION DISCLOSURE STATEMENT</b> <b>IN AN APPLICATION</b>	Docket Number: G&C 30794.94-US-WO	Application Number: 10/537,385
	Applicant: Benjamin A. Haskell et al.	
	Filing Date: June 3, 2005	Group Art Unit: <del>2814</del> 2824

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	Applicant: Benjamin A. Haskell et al.	
	Filing Date: June 3, 2005	Group Art Unit: <del>2011</del> 2824

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	Applicant: Benjamin A. Haskell et al.	
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	Applicant: Benjamin A. Haskell et al.	
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/ML/	6,177,057	01/2001	Purdy			
/ML/	6,156,581	12/2000	Vaudo et al.			
/ML/	5,926,726	07/1999	Bour et al.			
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	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
NON-PATENT DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
/ML/		Waltereit et al., "M-PLANE GaN(1 1 0 0) GROWN ON $\gamma$ -LiAlO <sub>2</sub> (1 0 0): NITRIDE SEMICONDUCTORS FREE OF INTERNAL ELECTROSTATIC FIELDS," <i>Journal of Crystal Growth</i> 227-228 (2001), pp. 437-441.				
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Sheet 1 of 1

<b>Form 1449*</b> <b>INFORMATION DISCLOSURE STATEMENT</b> <b>IN AN APPLICATION</b>	Docket Number: G&C 30794.94-US-WO	Application Number: 10/537,385
	Applicant: Benjamin A. Haskell et al.	
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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> ( Not for submission under 37 CFR 1.99)	Application Number		10537385	
	Filing Date		2005-06-03	
	First Named Inventor		Benjamin A. Haskell et al.	
	Art Unit		2841 2824	
	Examiner Name		<del>Steven Ho Yin Lok</del> Michael Lulis	
	Attorney Docket Number			

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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**  
( Not for submission under 37 CFR 1.99)

Application Number	10537385
Filing Date	2005-06-03
First Named Inventor	Benjamin A. Haskell et al.
Art Unit	<del>2844</del> 2824
Examiner Name	<del>Steven Ho Yin Lok</del> Michael Lulis
Attorney Docket Number	

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**EXAMINER SIGNATURE**

Examiner Signature	/Michael Lulis/	Date Considered	06/21/2007
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Date Mailed: January 15, 2007

Sheet 1 of 1

Form 1449*	Docket Number: GAC 30794.94-US-WO	Application Number: 10/537,383
INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION	Applicant: Benjamin A. Haskell et al.	
	Filing Date: June 3, 2005	Group Art Unit: <del>2044</del> 2824

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\*Substitute Disclosure Statement Form (PTO-1449)

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